

R1280D002x SERIES

2CH PWM DC/DC CONTROLLER

NO.EA-086-160125

OUTLINE

The R1280D002x Series are CMOS-based 2-channel PWM Step-up (as Channel 1)/Inverting (as Channel 2) DC/DC converter controllers.

Each of the R1280D002x Series consists of an oscillator, a PWM control circuit, a reference voltage unit, an error amplifier, a reference current unit, a protection circuit, and an under voltage lockout (UVLO) circuit. A high efficiency Step-up/Inverting DC/DC converter can be composed of this IC with inductors, diodes, power MOSFETs, resisters, and capacitors. Each Output Voltage can be adjustable with external resistors, while soft-start time can be adjustable with external capacitors.

Maximum Duty Cycle of R1280D002A and C series can be also adjustable with external resistors.

Maximum Duty Cycle of R1280D002B is built-in as 90%(Typ.).

When CE pin of R1280D002B is set at GND level, this IC turns off external power MOSFETs of Step-up/Inverting as Standby-mode.

Standby current is typically 0µA.

As for a protection circuit, if Maximum duty cycle of either Step-up DC/DC converter side or Inverting DC/DC converter side is continued for a certain time, the R1280D Series latch both external drivers with their off state by its Latch-type protection circuit. Delay time for protection is internally fixed typically at 100ms. To release the protection circuit, restart with power-on (Voltage supplier is equal or less than UVLO detector threshold level), or as for R1280D002B, once after making the circuit be stand-by with chip enable pin and enable the circuit again.

FEATURES

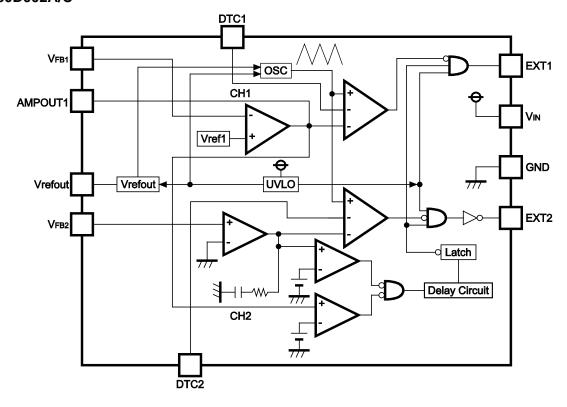
Input Voltage Range	2.5V to 5.5V
Built-in Latch-type Protection Function by mo	nitoring duty cycle (Fixed Delay Time Typ. 100ms)
Oscillator Frequency	700kHz (R1280D002A,B)/200kHz (R1280D002C)
Maximum Duty Cycle	Typ. 90% (Only applied to R1280D002B Series)
High Reference Voltage Accuracy	±1.5%
U.V.L.O. Threshold	Typ. 2.2V (Hysteresis: Typ. 0.1V)
Small Package	thin SON-10 (package thickness Max. 0.9mm)

APPLICATIONS

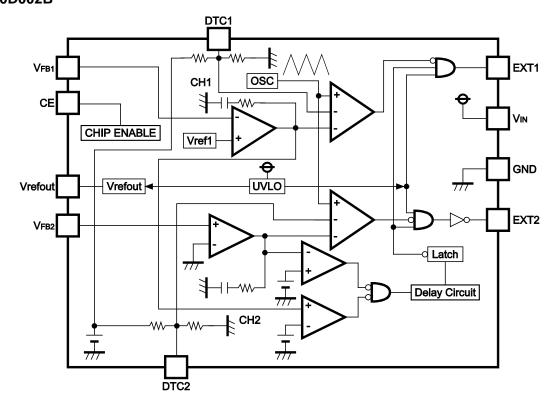
- Constant Voltage Power Source for Portable Equipment.
- Constant Voltage Power Source for LCD and CCD.

BLOCK DIAGRAM

• R1280D002A/C



• R1280D002B



SELECTION GUIDE

The mask option for the ICs can be selected at the user's request. The selection can be made with designating the part number as shown below;

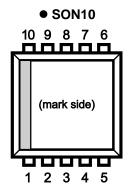
Selection Guide

Product Name	Package	Quantity per Reel	Pb Free	Halogen Free
R1280D002x-TR-FE	SON-10	3,000 pcs	Yes	Yes

x: Designation of Mask Option

A version: fosc=700kHz, with External Phase Compensation for Channel 1 B version: fosc=700kHz, with Internal Phase Compensation and standby mode C version: fosc=200kHz, with External Phase Compensation for Channel 1

PIN CONFIGURATION



PIN DESCRIPTION

• R1280D002A/C

Pin No	Symbol	Description
1	EXT1	External Transistor of Channel 1 Drive Pin (CMOS Output)
2	GND	Ground Pin
3	AMPOUT1	Amplifier Output Pin of Channel 1
4	DTC1	Maximum Duty Cycle of Channel 1 Setting Pin
5	V _{FB1}	Feedback pin of Channel 1
6	V _{FB2}	Feedback pin of Channel 2
7	DTC2	Maximum Duty Cycle of Channel 2 Setting Pin
8	Vrefout	Reference Output Pin
9	Vin	Voltage Supply Pin of the IC
10	EXT2	External Transistor of Channel 2 Drive Pin (CMOS Output)

• R1280D002B

Pin No	Symbol	Description
1	EXT1	External Transistor of Channel 1 Drive Pin (CMOS Output)
2	GND	Ground Pin
3	CE	Chip Enable Pin
4	DTC1	Soft-start Time of Channel 1 Setting Pin
5	V _{FB1}	Feedback pin of Channel 1
6	V _{FB2}	Feedback pin of Channel 2
7	DTC2	Soft-start Time of Channel 2 Setting Pin
8	Vrefout	Reference Output Pin
9	Vin	Voltage Supply Pin of the IC
10	EXT2	External Transistor of Channel 2 Drive Pin (CMOS Output)

ABSOLUTE MAXIMUM RATINGS

• R1280D002A/C

Symbol	Item	Rating	Unit
Vin	V _{IN} Pin Voltage	6.5	V
VEXT1,2	V _{EXT1,2} Pin Output Voltage	-0.3~Vin+0.3	V
V _{AMPOUT1}	AMPOUT1 Pin Voltage	-0.3~Vin+0.3	V
V _{DTC1,2}	DTC1,2 Pin Voltage	-0.3~Vin+0.3	V
Vrefout	VREFOUT Pin Voltage	-0.3~Vin+0.3	V
V _{FB1,2}	V _{FB1,VFB2} Pin Voltage	-0.3~Vin+0.3	V
I _{EXT1,2}	EXT1,2 Pin Output Current	±50	mA
P _D	Power Dissipation	250	mW
Topt	Operating Temperature Range	-40 to +85	°C
Tstg	Storage Temperature Range	-55 to +125	°C

• R1280D002B

Symbol	Item	Rating	Unit
Vin	V _{IN} Pin Voltage	6.5	V
VEXT1,2	V _{EXT1,2} Pin Output Voltage	-0.3~V _{IN} +0.3	V
Vce	CE Pin Voltage	-0.3~V _{IN} +0.3	V
V _{DTC1,2}	DTC1,2 Pin Voltage	-0.3~V _{IN} +0.3	V
Vrefout	VREFOUT Pin Voltage	-0.3~V _{IN} +0.3	V
V _{FB1,2}	V _{FB1} ,V _{FB2} Pin Voltage	-0.3~V _{IN} +0.3	V
lext1,2	EXT1,2 Pin Output Current	±50	mA
P _D	Power Dissipation	250	mW
Topt	Operating Temperature Range	-40 to +85	°C
Tstg	Storage Temperature Range	-55 to +125	°C

ELECTRICAL CHARACTERISTICS

• R1280D002A

Topt=25°C

Symbol	Item	Conditions	Min.	Тур.	Max.	Unit
VIN	Operating Input Voltage		2.5		5.5	V
VREFOUT	VREFOUT Voltage Tolerance	VIN=3.3V, IOUT=1mA	1.478	1.500	1.522	V
Irout	VREFOUT Output Current	VIN=3.3V	20			mA
ΔVREFOUT /ΔVIN	VREFOUT Line Regulation	$2.5V \le VIN \le 5.5V$		2	6	mV
ΔVREFOUT /ΔΙΟυΤ	VREFOUT Load Regulation	$1 \text{mA} \leq \text{Irout} \leq 10 \text{mA Vin=}3.3 \text{V}$		6	12	mV
Ішм	VREFOUT Short Current Limit	VIN=3.3V, VREFOUT=0V		25		mA
ΔV REFOUT/ ΔT	VREFOUT Voltage Temperature Coefficient	-40°C ≤ Topt ≤ 85°C		±150		ppm/°C
VFB1	VFB1 Voltage	VIN=3.3V	0.985	1.000	1.015	V
ΔV FB1/ ΔT	VFB1 Voltage Temperature Coefficient	-40°C ≤ Topt ≤ 85°C		±150		ppm/°C
IFB1,2	IFB1,2 Input Current	VIN=5.5V,VFB1 or VFB2=0V or 5.5V	-0.1		0.1	μA
fosc	Oscillator Frequency	EXT1,2 Pins at no load, VIN=3.3V	595	700	805	kHz
IDD1	Supply Current	VIN=5.5V, EXT1,2 pins at no load		1.4	3.0	mA
REXTH1	EXT1 "H" ON Resistance	VIN=3.3V, IEXT=-20mA		4.0	8.0	Ω
REXTL1	EXT1 "L" ON Resistance	VIN=3.3V, IEXT=20mA		2.7	5.0	Ω
REXTH2	EXT2 "H" ON Resistance	VIN=3.3V, IEXT=-20mA		4.0	8.0	Ω
REXTL2	EXT2 "L" ON Resistance	VIN=3.3V, IEXT=20mA		3.7	8.0	Ω
TDLY	Delay Time for Protection	VIN=3.3V, VFB1=1.1V→0V	60	100	140	ms
Vuvlod	UVLO Detector Threshold		2.10	2.20	2.35	V
Vuvlo	UVLO Released Voltage			VUVLOD +0.10	2.45	V
VDTC10	CH1 Duty=0%	VIN=3.3V	0.1	0.2	0.3	V
VDTC1100	CH1 Duty=100%	VIN=3.3V	1.1	1.2	1.3	V
VDTC20	CH2 Duty=0%	VIN=3.3V	0.1	0.2	0.3	V
VDTC2100	CH2 Duty=100%	VIN=3.3V	1.1	1.2	1.3	V
Av1	CH1 Open Loop Gain	VIN=3.3V		110		dB
FT1	CH1 Single Gain Frequency Band	VIN=3.3V, Av1=0dB		1.9		MHz
VICR1	CH1 Input Voltage Rang	VIN=3.3V		0.7 to VIN		V
IAMPL	CH1 Sink Current	VIN=3.3V, VAMPOUT1=1.0V, VFB1=VFB1+ 0.1V	70	115		μА
Іамрн	CH1 Source Current	VIN=3.3V, VAMPOUT1=1.0V, VFB1=VFB1- 0.1V		-1.4	-0.7	mA
Av2	CH2 Open Loop Gain	VIN=3.3V		60		dB
FT2	CH2 Single Gain Frequency Band	VIN=3.3V, AV2=0dB		3		MHz
VICR2	CH2 Input Voltage Range	VIN=3.3V		-0.2 to VIN-1.3		V
VFB2	CH2 Input Offset Voltage	VIN=3.3V	-12		12	mV



• R1280D002B

Topt=25°C

Symbol	Item	Conditions	Min.	Тур.	Max.	Unit
Vin	Operating Input Voltage		2.5		5.5	V
VREFOUT	VREFOUT Voltage Tolerance	VIN=3.3V, IOUT=1mA	1.478	1.500	1.522	V
IROUT	VREFOUT Output Current	VIN=3.3V	20			mA
ΔVREFOUT /ΔVIN	VREFOUT Line Regulation	2.5V ≦ VIN ≦ 5.5V		2	6	mV
ΔVREFOUT /Δ Ι ΟUT	VREFOUT Load Regulation	$1 \text{mA} \leq \text{Irout} \leq 10 \text{mA Vin=}3.3 \text{V}$		6	12	mV
Ішм	VREFOUT Short Current Limit	VIN=3.3V, VREFOUT=0V		25		mA
ΔVREFOUT /ΔT	VREFOUT Voltage Temperature Coefficient	-40°C ≦ Topt ≦ 85°C		±150		ppm/°C
VFB1	VFB1 Voltage	VIN=3.3V	0.985	1.000	1.015	V
ΔVFB1/ΔΤ	VFB1 Voltage Temperature Coefficient	-40°C ≦ Topt ≦ 85°C		±150		ppm/°C
IFB1,2	IFB1,2 Input Current	VIN=5.5V,VFB1 or VFB2=0V or 5.5V	-0.1		0.1	μΑ
fosc	Oscillator Frequency	EXT1,2 Pins at no load, VIN=3.3V	595	700	805	kHz
IDD1	Supply Current	VIN=5.5V, EXT1,2 pins at no load		1.4	3.0	mA
Maxdty	Maximum Duty Cycle	VIN=3.3V, CDTC1,2=1000pF	84	90	95	%
Rexth1	EXT1 "H" ON Resistance	VIN=3.3V, IEXT=-20mA		4.0	8.0	Ω
REXTL1	EXT1 "L" ON Resistance	VIN=3.3V, IEXT=20mA		2.7	5.0	Ω
REXTH2	EXT2 "H" ON Resistance	VIN=3.3V, IEXT=-20mA		4.0	8.0	Ω
REXTL2	EXT2 "L" ON Resistance	VIN=3.3V, IEXT=20mA		3.7	8.0	Ω
TDLY	Delay Time for Protection	VIN=3.3V, VFB1=1.1V→0V	60	100	140	ms
Tss1	Soft Start Time1 for Ch1	VIN=3.3V, CDTC1=0.33μF		10		ms
Tss2	Soft Start Time2 for Ch2	VIN=3.3V, CDTC2=0.33μF		15		ms
VCEH	CE "H" Input Voltage	VIN=5.5V	1.5			V
VCEL	CE "L" Input Voltage	VIN=2.5V			0.3	V
Vuvlod	UVLO Detector Threshold		2.10	2.20	2.35	V
Vuvlo	UVLO Released Voltage			VUVLOD +0.10	2.45	V
Ісен	CE "H" Input Current	VIN= VCE=5.5V	-0.1		0.1	μΑ
ICEL	CE "L" Input Current	VIN=5.5V, VCE=0.0V	-0.1		0.1	μΑ
Іѕтв	Standby Current	VIN=5.5V, VCE=0.0V		0	2	μА
Voff2	Input Offset Voltage of Ch2.	VIN=3.3V	-12		12	mV

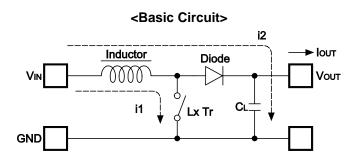
• R1280D002C

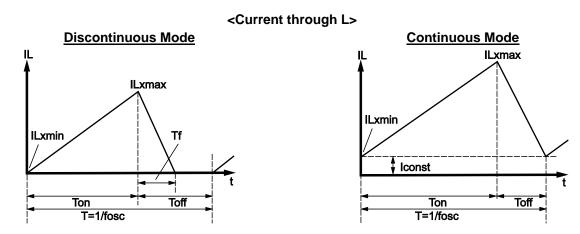
Topt=25°C

Symbol	ltem	Conditions	Min.	Тур.	Max.	Unit
Vin	Operating Input Voltage		2.5		5.5	V
VREFOUT	VREFOUT Voltage Tolerance	VIN=3.3V, IOUT=1mA	1.478	1.500	1.522	V
Irout	VREFOUT Output Current	VIN=3.3V	20			mA
ΔVREFOUT/ΔVIN	VREFOUT Line Regulation	$2.5V \le VIN \le 5.5V$		2	6	mV
ΔVREFOUT /ΔΙουτ	VREFOUT Load Regulation	$1 \text{mA} \leq \text{Irout} \leq 10 \text{mA Vin=}3.3 \text{V}$		6	12	mV
Ішм	VREFOUT Short Current Limit	VIN=3.3V, VREFOUT=0V		25		mA
ΔV REFOUT/ ΔT	VREFOUT Voltage Temperature Coefficient	-40°C ≦ Topt ≦ 85°C		±150		ppm/°C
VFB1	VFB1 Voltage	VIN=3.3V	0.985	1.000	1.015	V
ΔVfb1/ΔT	VFB1 Voltage Temperature Coefficient	-40 °C \leq Topt \leq 85°C		±150		ppm/°C
IFB1,2	IFB1,2 Input Current	VIN=5.5V,VFB1 or VFB2=0V or 5.5V	-0.1		0.1	μА
fosc	Oscillator Frequency	EXT1,2 Pins at no load, VIN=3.3V	160	200	240	kHz
IDD1	Supply Current	VIN=5.5V, EXT1,2 pins at no load		0.7	1.2	mA
Rexth1	EXT1 "H" ON Resistance	VIN=3.3V, IEXT=-20mA		4.0	8.0	Ω
REXTL1	EXT1 "L" ON Resistance	VIN=3.3V, IEXT=20mA		2.7	5.0	Ω
REXTH2	EXT2 "H" ON Resistance	VIN=3.3V, IEXT=-20mA		4.0	8.0	Ω
REXTL2	EXT2 "L" ON Resistance	VIN=3.3V, IEXT=20mA		3.7	8.0	Ω
TDLY	Delay Time for Protection	VIN=3.3V, VFB1=1.1V→0V	50	100	150	ms
Vuvlod	UVLO Detector Threshold		2.10	2.20	2.35	V
Vuvlo	UVLO Released Voltage			VUVLOD +0.10	2.45	V
VDTC10	CH1 Duty=0%	VIN=3.3V	0.15	0.25	0.35	V
VDTC1100	CH1 Duty=100%	VIN=3.3V	1.1	1.2	1.3	V
VDTC20	CH2 Duty=0%	VIN=3.3V	0.15	0.25	0.35	V
VDTC2100	CH2 Duty=100%	VIN=3.3V	1.1	1.2	1.3	V
Av1	CH1 Open Loop Gain	VIN=3.3V		110		dB
FT1	CH1 Single Gain Frequency Band	VIN=3.3V, Av1=0dB		1.9		MHz
VICR1	CH1 Input Voltage Range	VIN=3.3V		0.7 to VIN		V
IAMPL	CH1 Sink Current	VIN=3.3V, VAMPOUT1=1.0V, VFB1=VFB1+ 0.1V	70	115		μА
Іамрн	CH1 Source Current	VIN=3.3V, VAMPOUT1=1.0V, VFB1=VFB1- 0.1V		-1.4	-0.7	mA
Av2	CH2 Open Loop Gain	VIN=3.3V		60		dB
FT1	CH2 Single Gain Frequency Band	VIN=3.3V, Av2=0dB		3		MHz
VICR1	CH2 Input Voltage Range	VIN=3.3V		-0.2 to VIN-1.3		V
VFB2	CH2 Input Offset Voltage	VIN=3.3V	-12		12	mV

Operation of Step-up DC/DC Converter and Output Current

Step-up DC/DC Converter makes higher output voltage than input voltage by releasing the energy accumulated during on time of Lx Transistor on input voltage.





- Step 1. Lx Tr. is on, then the current IL=i1 flows, and the energy is charged in L. In proportion to the on time of Lx Tr. (Ton), IL=i1 increases from IL=ILxmin=0 and reaches ILxmax.
- Step 2. When the Lx Tr. is off, L turns on Schottky Diode (SD), and IL=i2 flows to maintain IL=ILxmax.
- Step 3. IL=i2 gradually decreases, and after Tf passes, IL=ILxmin=0 is true, then SD turns off. Note that in the case of the continuous mode, before IL=ILxmin=0 is true, Toff passes, and the next cycle starts, then Lx Tr. turns on again.

In this case, ILxmin>0, therefore IL=ILxmin>0 is another starting point and ILx max increases.

With the PWM controller, switching times during the time unit are fixed. By controlling Ton, output voltage is maintained.

Output Current and Selection of External Components

Output Current of Step-up Circuit and External Components

There are two modes, or discontinuous mode and continuous mode for the PWM step-up switching regulator depending on the continuous characteristic of inductor current.

During on time of the transistor, when the voltage added on to the inductor is described as V_{IN} , the current is $V_{IN} \times t/L$.

Therefore, the electric power, Pon, which is supplied with input side, can be described as in next formula.

$$P_{ON} = \int_{0}^{T_{ON}} V_{IN}^{2} \times t/L \ dt$$
 Formula 1

With the step-up circuit, electric power is supplied from power source also during off time. In this case, input current is described as (Vout-Vin)×t/L, therefore electric power, Poff is described as in next formula.

$$P_{OFF} = \int_{0}^{Tf} V_{IN} \times (V_{OUT} - V_{IN}) t/L dt$$
 Formula 2

In this formula, Tf means the time of which the energy saved in the inductance is being emitted. Thus average electric power, P_{AV} is described as in the next formula.

$$P_{AV} = 1/(Ton + Toff) \times \{ \int_0^{Ton} V_{IN}^2 \times t/L \ dt + \int_0^{Tf} V_{IN} \times (V_{OUT} - V_{IN})t/L \ dt \}$$
 Formula 3

In PWM control, when Tf=Toff is true, the inductor current becomes continuos, then the operation of switching regulator becomes continuous mode.

In the continuous mode, the deviation of the current is equal between on time and off time.

Further, the electric power, Pav is equal to output electric power, Voutxlout, thus,

$$lout = fosc \times Vin^2 \times Ton^2 / \{2 \times L \times (Vout - Vin)\} = Vin^2 \times Ton / (2 \times L \times Vout)$$
 Formula 5

When I_{OUT} becomes more than $V_{\text{IN}}\times\text{Ton}\times\text{Toff}/(2\times L\times(\text{Ton}+\text{Toff}))$, the current flows through the inductor, then the mode becomes continuous. The continuous current through the inductor is described as Iconst, then,

$$lout = fosc \times Vin^2 \times Ton^2/(2 \times L \times (Vout - Vin)) + Vin \times Iconst/Vout \dots Formula 6$$

In this moment, the peak current, ILxmax flowing through the inductor and the driver Tr. is described as follows: $ILxmax = Iconst + V_{IN} \times Ton/L$ Formula 7 With the formula 4,6, and ILxmax is, $ILxmax = V_{OUT}/V_{IN} \times I_{OUT} + V_{IN} \times Ton/(2 \times L)$ Formula 8

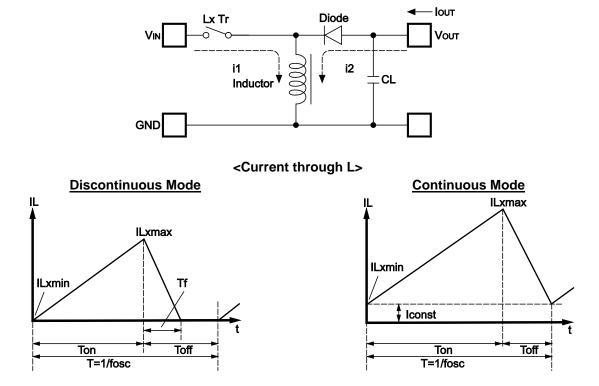
Therefore, peak current is more than IouT. Considering the value of ILxmax, the condition of input and output, and external components should be selected.

In the formula 7, peak current ILxmax at discontinuous mode can be calculated. Put Iconst=0 in the formula.

The explanation above is based on the ideal calculation, and the loss caused by Lx switch and external components is not included. The actual maximum output current is between 50% and 80% of the calculation. Especially, when the ILx is large, or V_{IN} is low, the loss of V_{IN} is generated with the on resistance of the switch. As for V_{OUT} , Vf (as much as 0.3V) of the diode should be considered.

Operation of Inverting DC/DC converter and Output Current

Inverting DC/DC converter saves energy during on time of Lx transistor, and supplies the energy to output during off time, output voltage opposed to input voltage is obtained.



Step 1. Lx Tr. turns on, current, IL=i1 flows, energy is charged in L. In proportion to the on time, Ton, of Lx Tr. IL=i1 increases from IL=ILxmin=0 and reaches ILxmax.

- Step 2. When the Lx Tr. turns off, L turns on Shottky diode (SD) and flow IL=i2 to maintain IL = ILxmax.
- Step 3. IL=i2 decreases gradually, after Tf passes, IL=ILxmin=0 is true, then SD turns off. Note that in the case of continuous mode, before IL=ILxmin=0 is true, Toff passes and next cycle starts, then Lx Tr. turns on. In this case, ILxmin>0, therefore IL increases from IL=ILxmin>0.

With the PWM controller, switching time (fosc) in the time unit is fixed, and by controlling Ton, output voltage is maintained.

Output Current and Selection of External Components

There are also two modes, or discontinuous mode and continuous mode for the PWM inverting switching regulator depending on the continuous characteristic of inductor current.

During on time of the transistor, when the voltage added on to the inductor is described as V_{IN} , the current is $V_{IN} \times t/L$.

Therefore, the electric power, P, which is supplied with input side, can be described as in next formula.

$$P = \int_0^{Ton} V_{IN}^2 \times t/L \ dt$$
 Formula 9

Thus average electric power in one cycle, PAV is described as in the next formula.

$$P_{AV} = 1/(Ton + Toff) \times \int_0^{Ton} V_{IN}^2 \times t/L \ dt = V_{IN}^2 \times Ton^2/(2 \times L \times (Ton + Toff)) \qquad Formula \ 10$$

This electric power Pav equals to output electric power Vout × lout, thus,

$$I_{OUT} = f_{OSC} \times V_{IN}^2 \times Ton^2/(2 \times L \times V_{OUT})$$
 Formula 11

When I_{OUT} becomes more than $V_{\text{IN}} \times \text{Ton} \times \text{Toff} / (2 \times L \times (\text{Ton} + \text{Toff}))$, the current flows through the inductor continuously, then the mode becomes continuous. In the continuous mode, the deviation of the current equals between Ton and Toff, therefore,

In this moment, the current flowing continuously through L, is assumed as Iconst, IouT is described as in the next formula:

In this moment, the peak current, ILxmax flowing through the inductor and the driver Tr. is described as follows:

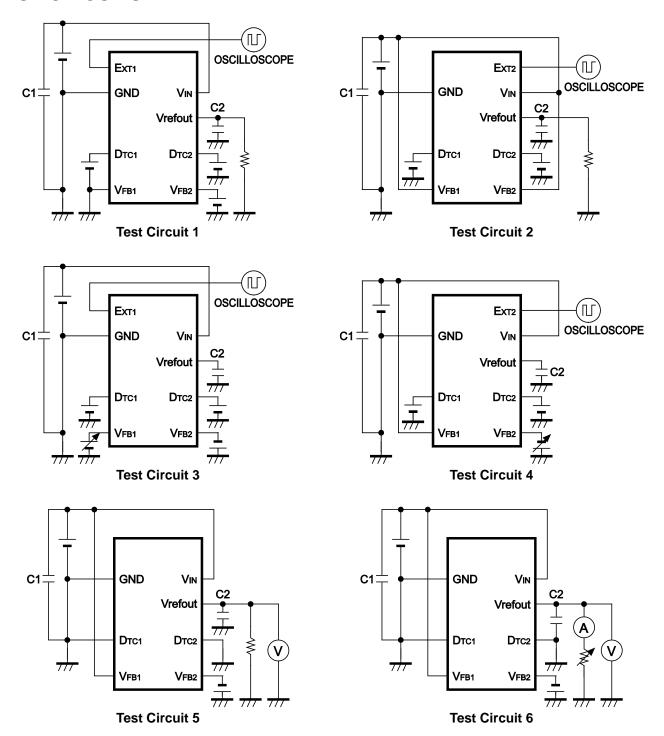
With the formula 12,13, ILxmax is,

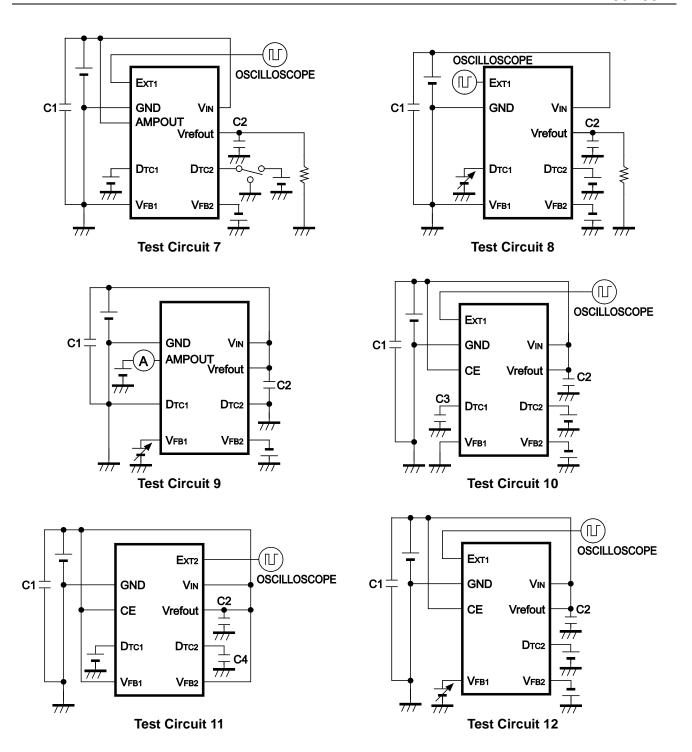
Therefore, peak current is more than IouT. Considering the value of ILxmax, the condition of input and output, and external components should be selected.

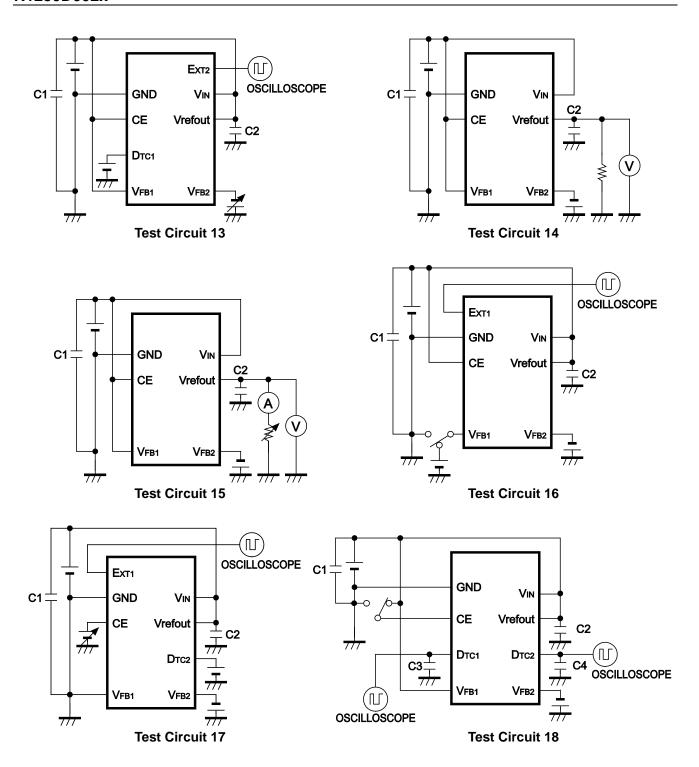
In the formula 14, peak current ILxmax at discontinuous mode can be calculated. Put Iconst=0 in the formula.

The explanation above is based on the ideal calculation, and the loss caused by Lx switch and external components is not included. The actual maximum output current is between 50% and 80% of the calculation. Especially, when the ILx is large, or V_{IN} is low, the loss of V_{IN} is generated with the on resistance of the switch. As for V_{OUT} , Vf (as much as 0.3V) of the diode should be considered.

TEST CIRCUITS







Typical Characteristics shown in the following pages are obtained with test circuits shown above.

R1280D002A/C

Test Circuit 1,2: ypical Characteristic 4) Test Circuit 3: Typical Characteristic 6) Test Circuit 4: Typical Characteristic 7) Test Circuit 5: Typical Characteristic 8) Typical Characteristics 9) 10) Test Circuit 6: Test Circuit 7: Typical Characteristic 11) Test Circuit 8: Typical Characteristic 12) Test Circuit 9: Typical Characteristics 13) 14)

R1280D002B

Test Circuit 10,11: Typical Characteristics 4) 5)
Test Circuit 12: Typical Characteristic 6)
Test Circuit 13: Typical Characteristic 7)
Test Circuit 14: Typical Characteristic 8)
Test Circuit 15: Typical Characteristics 9) 10)
Test Circuit 16: Typical Characteristics 11)
Test Circuit 17: Typical Characteristics 15) 16)
Test Circuit 18: Typical Characteristics 17) 18)

Standard Circuit Example: Typical Characteristics 1) 2) 3) 19) 20)

Note) Capacitors' values of test circuits

Capacitors: Ceramic Type:

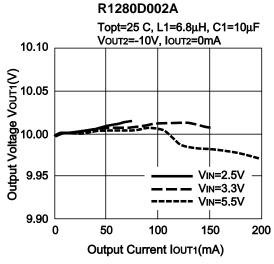
C1=4.7µF, C2=1.0µF, C3=C4=1000pF

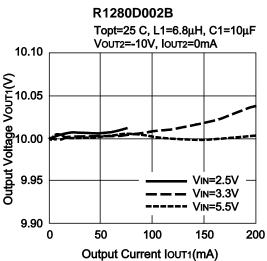
Efficiency $\eta(\%)$ can be calculated with the next formula:

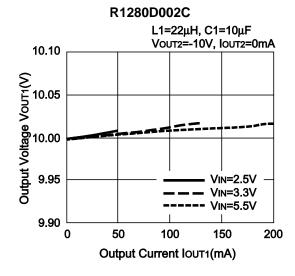
 $\eta = (V_{\text{OUT1}} \times I_{\text{OUT1}} + V_{\text{OUT2}} \times I_{\text{OUT2}})/(V_{\text{IN}} \times I_{\text{IN}}) \times 100$

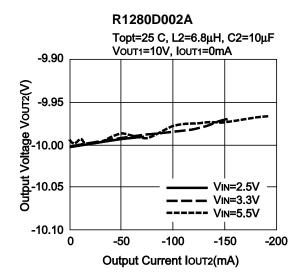
TYPICAL CHARACTERISTICS

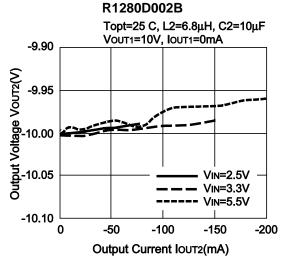
1) Output Voltage vs. Output Current

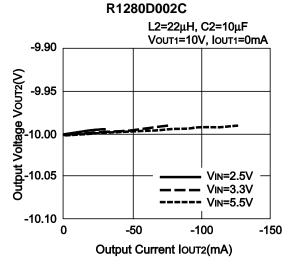




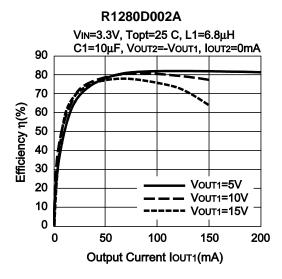




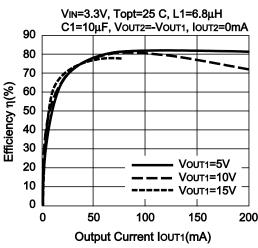




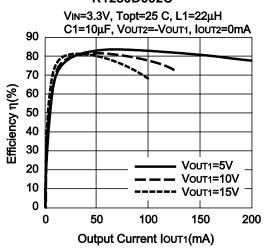
2) Efficiency vs. Output Current



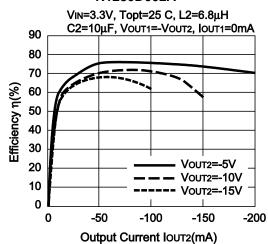




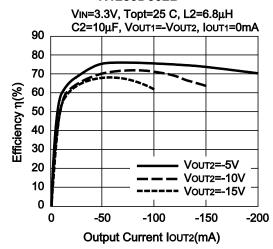
R1280D002C



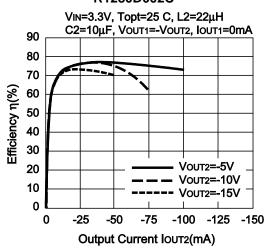
R1280D002A



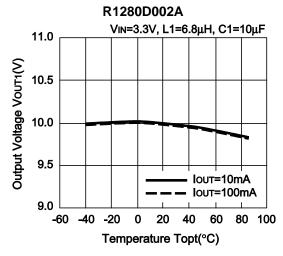
R1280D002B

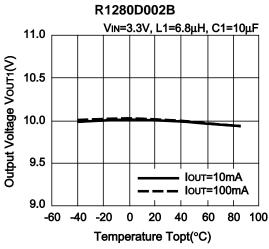


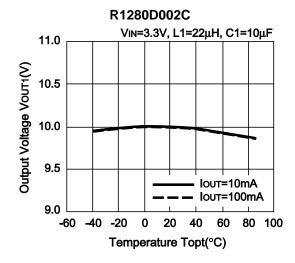
R1280D002C

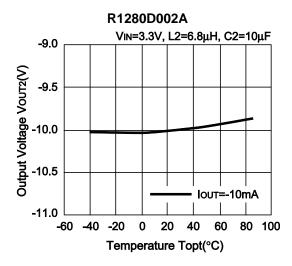


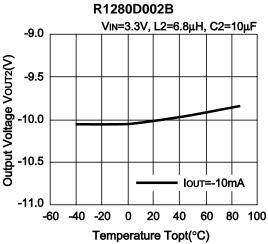
3) Output Voltage vs. Temperature

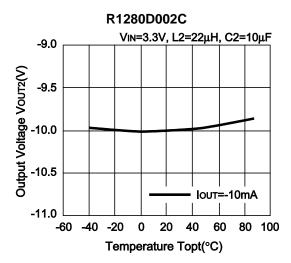




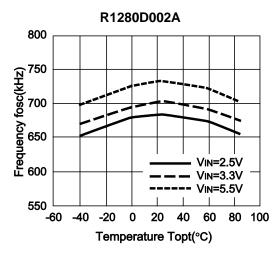


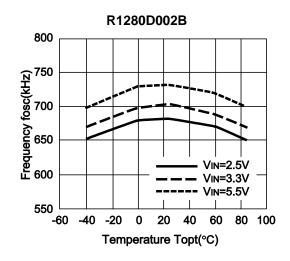


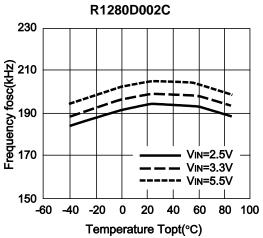




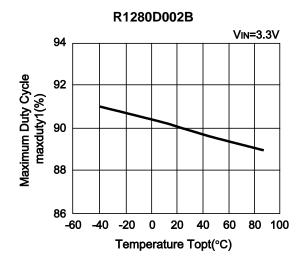
4) Frequency vs. Temperature

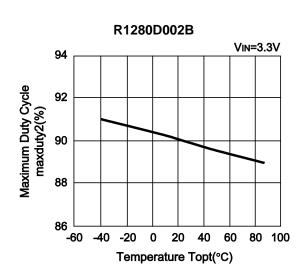




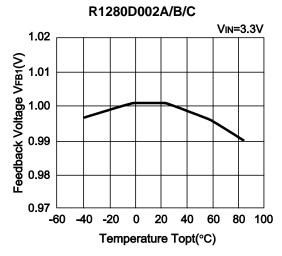


5) Maximum Duty Cycle vs. Temperature

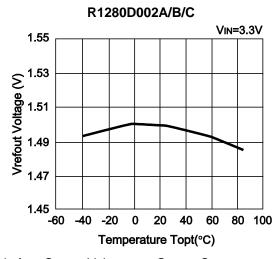




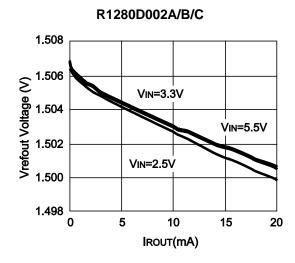
6) Feedback Voltage vs. Temperature



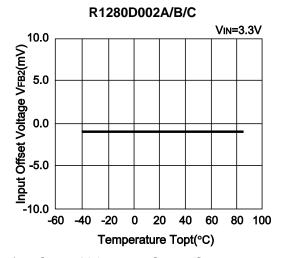
8) Vrefout Output Voltage vs. Temperature



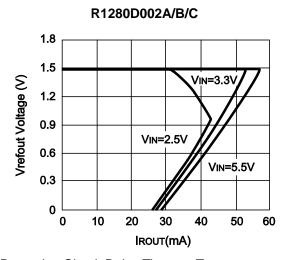
10) Vrefout Output Voltage vs. Output Current



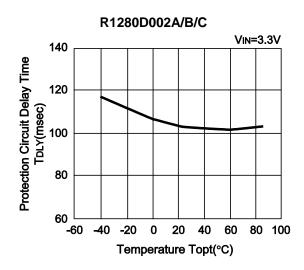
7) Input Offset Voltage vs. Temperature



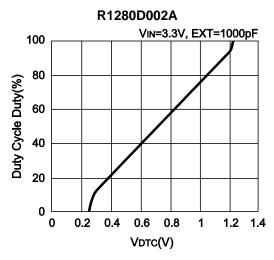
9) Vrefout Output Voltage vs. Output Current

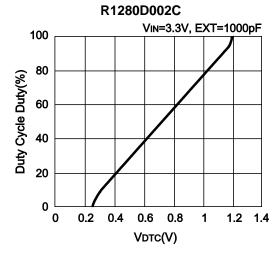


11) Protection Circuit Delay Time vs. Temperature



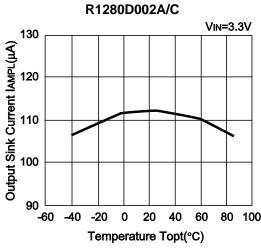
12) Duty Cycle vs. DTC Voltage

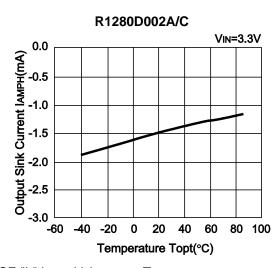




13) Output Sink Current vs. Temperature

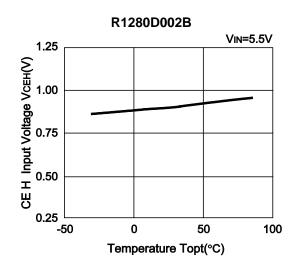


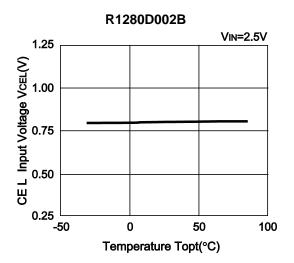




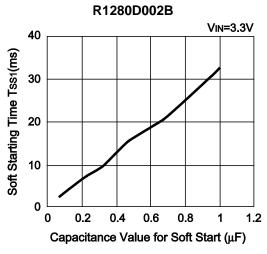
15) CE "H" Input Voltage vs. Temperature



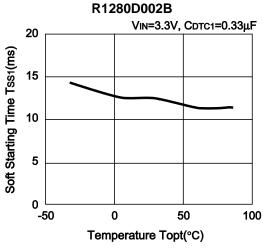




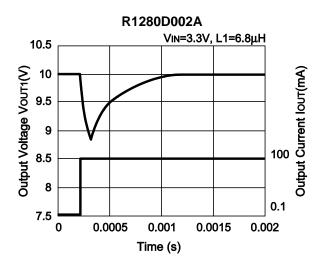
17) Soft Starting Time vs. Capacitance value

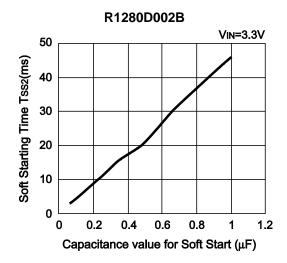


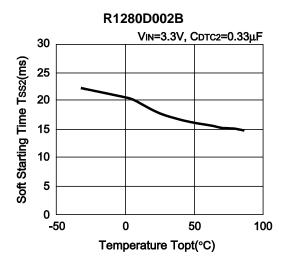
18) Soft Starting Time vs. Temperature

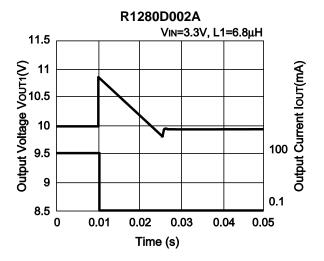


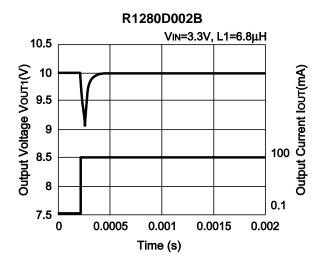
19) Load Transient Response(Step-up Side)

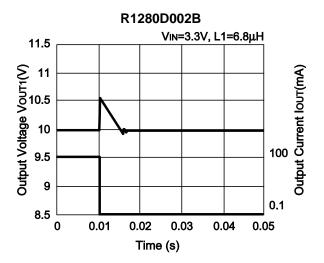


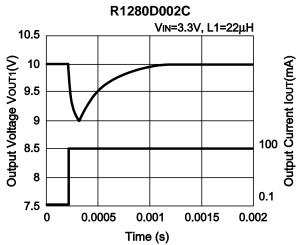


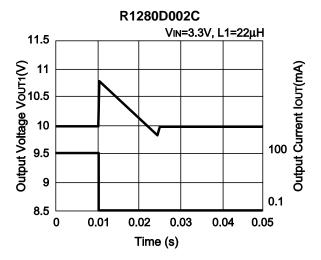




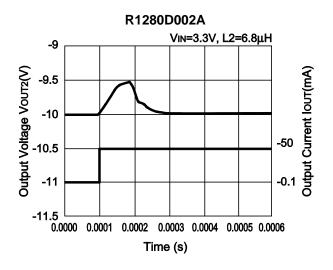


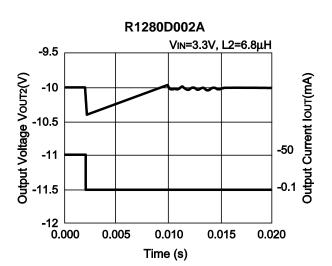


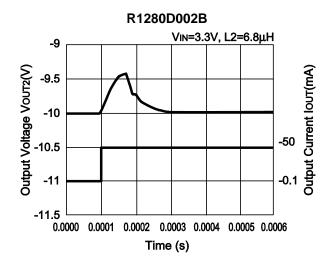


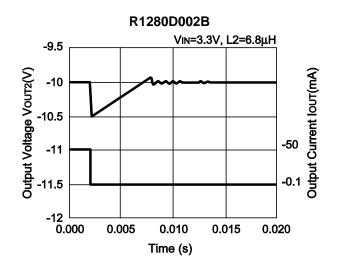


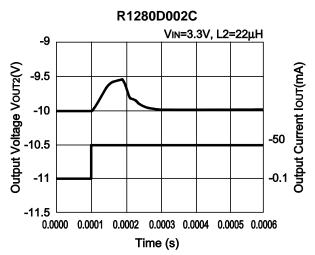
20) Load Transient Response (Inverting Side)

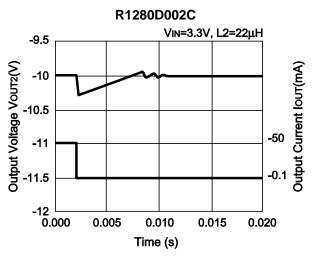






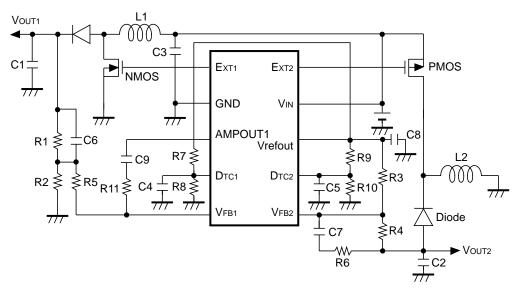






TYPICAL APPLICATION AND TECHNICAL NOTES

• R1280D002A/C



External Components

Inductor L1,2: 6.8 µH, VLF504012MT (TDK) for A type, 22 µH for C type

Diode: CRS10I30A (Toshiba)

NMOS: IRF7601 (International Rectifier)

PMOS: Si3443DV (Siliconix)

Resistors: R1, R2, R3, and R4 are for Setting Output Voltage. Recommendation values are

 $R1+R2\leq100k\Omega$ or $R3+R4\leq100k\Omega$

R5=43k Ω , R6=10k Ω , R7=R9=22k Ω , R8=R10=43k Ω , R11=220k Ω

Capacitors: Ceramic Capacitor

(Example)

R1280D002A: C1=C2=10 μ F, C3=4.7 F, C4=0.22 μ F, C5=0.47 μ F, C6=120pF, C7=50pF,

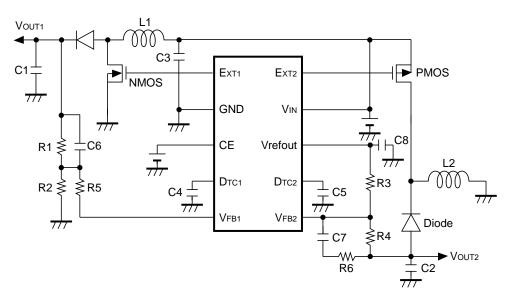
C8=1µF, C9=1000pF

R1280D002C: C1=C2=10 F, C3=4.7 μ F, C4=0.22 μ F, C5=0.47 μ F, C6=220pF, C7=330pF,

C8=1µF, C9=1000pF

Note: Maximum voltage tolerance of each component should be considered. With the transistor shown above is appropriate to set up to $\pm 15V$ as output voltage.

• R1280D002B



External Components

 $Inductor\ L1,2:\quad 6.8\mu H,\ VLF504012MT\ (TDK)$

Diode: CRS10I30A (Toshiba)

NMOS: IRF7601 (International Rectifier)

PMOS: Si3443DV (Siliconix)

Resistors: R1, R2, R3, and R4 are for Setting Output Voltage. Recommendation values are

R1+R2≤100k Ω or R3+R4≤100k Ω

R5=43k Ω , R6=10k Ω

Capacitors: Ceramic Capacitor

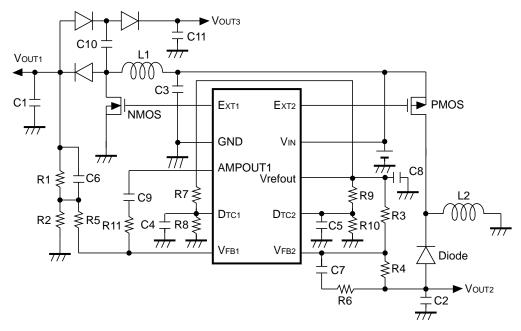
(Example)

 $C1=C2=10\mu F,\ C3=4.7\mu F,\ C4=0.33\mu F,\ C5=0.33\mu F,\ C6=120p F,\ C7=50p F,\ C8=1\mu F$

Note: Maximum voltage tolerance of each component should be considered. With the transistor shown above is appropriate to set up to $\pm 15V$ as output voltage.

APPLICATION EXAMPLE

R1280D002A/C



External Components

Inductor L1,2: $6.8\mu H$, VLF504012MT (TDK) for A version, $22\mu H$ for R1280D002C

Diode: CRS10I30A (Toshiba)

NMOS: IRF7601 (International Rectifier)

PMOS: Si3443DV (Siliconix)

Resistors: R1, R2, R3, and R4 are for Setting Output Voltage. Recommendation values are

 $R1+R2\leq100k\Omega$ or $R3+R4\leq100k\Omega$

R5=43k Ω , R6=10k Ω , R7=R9=22k Ω , R8=R10=43k Ω , R11=220k Ω

Capacitors: Ceramic Capacitor

(Example)

R1280D002A: $C1=C2=10\mu F, C3=4.7\mu F, C4=0.22$ F, C5=0.47 $\mu F, C6=120p F, C7=50p F, C7$

C8=C10=C11=1µF, C9=1000pF

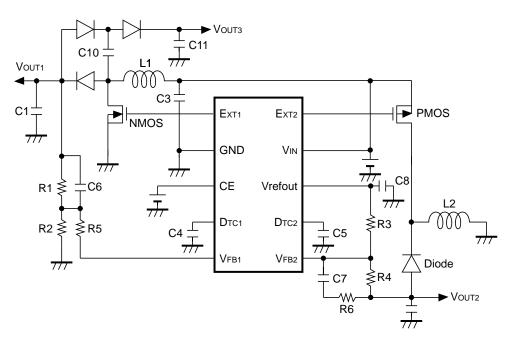
R1280D002C: C1=C2=10 μ F, C3=4.7 μ F, C4=0.22 μ F, C5=0.47 μ F, C6=220 μ F, C7=330 μ F, C7=330 μ F, C4=0.22 μ F, C5=0.47 μ F, C6=220 μ F, C7=330 μ F, C7=330 μ F, C4=0.22 μ F, C5=0.47 μ F, C6=220 μ F, C7=330 μ

C8=C10=C11=1µF, C9=1000pF

This IC can be used 3 Output TFT Bias Circuit as shown above. Vout3=2xVout1-Vf

Note: Maximum voltage tolerance of each component should be considered. With the transistor shown above is appropriate to set up to +15V as Vout1, -15V as Vout2, 30V as Vout3.

• R1280D002B



External Components

Inductor L1,2: 6.8 µH, VLF504012MT (TDK)
Diode: CRS10I30A (Toshiba)

NMOS: IRF7601 (International Rectifier)

PMOS: Si3443DV (Siliconix)

Resistors: R1, R2, R3, and R4 are for Setting Output Voltage. Recommendation values are

R1+R2 $100k\Omega$ or R3+R4 $100k\Omega$, R5=43 $k\Omega$, R6= $10k\Omega$,

Capacitors: Ceramic Capacitor

(Example)

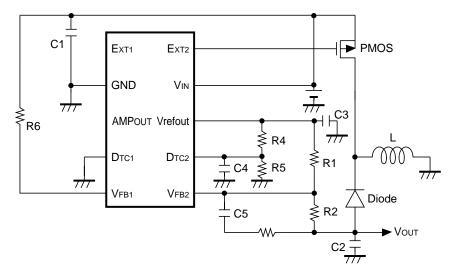
R1280D002B: $C1=C2=10\mu F$, $C3=4.7\mu F$, $C4=0.22\mu F$, $C5=0.33\mu F$, C6=120p F, C7=50p F,

 $C8=C10=C11=1\mu F$

This IC can be used 3 Output TFT Bias Circuit as shown above. Vout3=2xVout1-Vf

Note: Maximum voltage tolerance of each component should be considered. The transistor shown above is appropriate to set up to +15V as Vout1, -15V as Vout2, 30V as Vout3

R1280D002A/C



Components examples

Inductor L: 6.8μH VLF504012MT (TDK) (R1280D002C: 22μH)

Diode: CRS10I30A (Toshiba) PMOS: Si3443DV (Siliconix)

Resistance: As setting resistors total value for the output voltage, R1+R2 should be $100k\Omega$ or less.

R1=10k Ω R2=68k Ω R3=10k Ω R4=22k Ω

R5=43k Ω R6=1k Ω

*In the circuit above, output, VouT=-10V

Capacitors Ceramic Type

R1280D002A Ex.)

 $C1=4.7\mu F$ $C2=10\mu F$ $C3=1\mu F$ $C4=0.47\mu F$ C5=50pF

R1280D002C Ex.)

 $C1=4.7\mu F$ $C2=10\mu F$ $C3=1\mu F$ $C4=0.47\mu F$ C5=330pF

As for R1280D002B, when DTC1 is OPEN and V_{FB1}=V_{DD}, then the R1280D002B can be used as an inverting controller without step-up channel.

Note: Consider the ratings of external components including voltage tolerance. With the transistor in the circuit above, Vout=-15V is the voltage setting limit.

If this IC is used as an inverting controller without step-up channel, Vrefout pin and V_{FB1}, DTC1 pin should not connect one another. Both the direct connection and via resistor are not permitted.

EXTERNAL COMPONENTS

1. How to set the output voltages

As for step-up side, feedback (VFB1) pin voltage is controlled to maintain 1V, therefore,

Vout1: R1+R2=VFB1: R2

Thus, $V_{OUT1}=V_{FB1}\times (R1+R2)/R2$

Output Voltage is adjustable with R1 and R2.

As for inverting side, Feedback (VFB2) pin voltage is controlled to maintain 0V, therefore,

Vrefout: R3=|-Vout2|:R4

Thus, |-Vout2|=Vrefout×R4/R3

Output Voltage is adjustable with R3 and R4.

2. How to set Soft-Start Time

As for R1280D002B, soft-start time is adjustable with connecting a capacitor to DTC pin.

Soft starting time, Tss1 and Tss2 are adjustable. Soft-start time can be set with the time constant of RC.

Soft-start time can be described as in next formula. (Topt=25°C)

 $Tss1\cong RS1\times C4$, $Tss2\cong RS2\times C5$

In the above formulas, RS1 value is Typ. $32k\Omega$, while RS2 value is Typ. $45k\Omega$. Tolerance of these values is $\pm 25\%$ caused by dispersion of wafer process parameters.

On the other hand, as for R1280D002A/C, each soft-start time is set with the time constant of each external resistors and capacitor shown as in the next formula.

 $T_{SS1}\cong R_{O1}\times C4$, $T_{SS2}\cong R_{O2}\times C5$

In the above formula, $Ro_1=(R7\times R8)/(R7+R8)$, $Ro_2=(R9\times R10)/(R9+R10)$

TECHNICAL NOTES on EXTERNAL COMPONENTS

- External components should be set as close to this IC as possible. Especially, wiring of the capacitor connected to V_{IN} pin should be as short as possible.
- Enforce the ground wire. Large current caused by switching operation flows through GND pin. If the impedance of ground wire is high, internal voltage level of this IC might fluctuate and operation could be unstable.
- Recommended capacitance value of C3 is equal or more than 4.7μF. Recommended maximum voltage tolerance of C3 is three times as large as set output voltage or more, because the external transistor might generate a high voltage with a shape of spike because of an effect from inductor.
- If the spike noise of Vout is too large, the noise is feedback from V_{FB1} pin and operation might be unstable.
 In that case, use the resistor ranging from 10kΩ to 50kΩ as R5 and try to reduce the noise level. In the case of Vout2, use the resistor as much as 10kΩ as R6.
- Select an inductor with low D.C. current, large permissible current, and uneasy to cause magnetic saturation. If the inductance value is too small, ILx might be beyond the absolute maximum rating at the maximum load.
- Select a Schottky diode with fast switching speed and large enough permissible current.
- Recommended capacitance value of C1 and C2 is as much as Ceramic 10μF. In case that the operation with
 the system of DC/DC converter would be unstable, add a series resister less than 0.5Ω to each output
 capacitor or use tantalum capacitors with appropriate ESR. If you choose too large ESR, ripple noise may
 be forced to V_{FB1} and V_{FB2}, and unstable operation may result. Use a capacitor with three times as large as
 voltage tolerance of the capacitor.
- In this IC, for the test efficiency, Latch release function is included. By forcing (V_{IN}-0.3)V or more voltage to DTC1 pin or DTC2 pin, Latch release function works.
- Consider the threshold voltage of Power MOSFET transistor. Select an appropriate MOSFET transistor, depending on the input voltage in order to make the MOSFET turn on completely.
- Performance of the power controller with using this IC depends on external components. Each component, layout should not be beyond each absolute maximum rating such as voltage, current, and power dissipation.



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